IN THE SPECIFICATION:

Paragraph beginning at line 3 of page 1 has been amended as follows:

The present invention relates to a wafer pattern observation method and device ~~that determines~~ for determining observation positions using CAD data.

Paragraph beginning at line 25 of page 1 has been amended as follows:

Accordingly, the conventional wafer pattern observation method involves the following ~~problems.~~ problems: (1) In checking that the pattern formed on the wafer is adequate, it is necessary to set a considerable number of control points, but it is impossible for an operator to perform setting of the necessary control points across a number of places relying on ~~their~~ his intuition and ~~experience,~~ experience and, as a result, it is not possible to realize reliable pattern observation. (2) Since the determination of the observation positions relies on manual operation, it takes time to determine the observation positions, which is bad from the point of view of working efficiency. In particular, there is a noticeable lowering of working efficiency when observing multiple products.

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(3) Since the wafer pattern observation device is operated manually to perform necessary pattern observation, the pattern observation takes time, which is not efficient.

Paragraph beginning at line 12 of page 2 has been amended as follows:

An object of the present invention is to provide a wafer pattern observation method and device that can solve the problems described above ~~that exist in~~ <u>in connection with</u> the related art.

Heading at line 16 of page 4 has been amended as follows:

DETAILED ~~DISCRIPTION~~ <u>DESCRIPTION</u> OF THE PREFERRED EMBODIMENTS

Paragraph beginning at 23 of page 4 has been amended as follows:

In a wafer pattern observation system 1, numeral 2 indicates a stage and numeral 3 indicates a pattern observation device body, and a <u>positioning or</u> navigation unit 5 is provided for enlarging specified locations of a pattern (not shown) formed on a wafer 4 set on the stage 2 at a high magnification factor for observation with the pattern observation body 3. CAD graphics data of a pattern formed on the wafer 4 is stored in an externally provided memory 6.

Paragraph beginning at line 24 of page 9 has been amended as follows:

A device is made on a computer based on CAD graphics data, and a plurality of control points are determined from the view point of the electrical characteristics of the device.

(2) Process Simulation. Process simulation is carried out with gas diffusion time or gas amount for pattern formation as parameters, and problematic points of the formed pattern are ascertained to determine a plurality of control points.

(3) Etching Simulation. A removal is simulated with exposure or etching fluid diffusion for pattern formation as parameters, problematic points are ascertained from that standpoint to determine a plurality of control points.

(4) CAD ~~pattern density~~ Pattern Density. The density of aggregates of pattern formation, portions at positions changing from high density to low density, problematic points in the case of pattern formation from an exposure image etc. are ascertained to determine a plurality of control points.